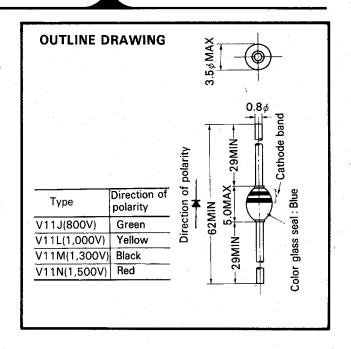
TYPE V11

FEATURES

- •V11 is a device developed for switching applications, with a reverse recovery time of 0.4μsec. This product is optimum for use in high-frequency circuits such as television horizontal deflection circuits.
- Due to employment of the glass encapsulation that gained high repute in V03/V06, great convenience is provided for build-in wiring.
- Because of strict quality control and steady mass production, this diode offers uniform characteristics and remarkably high reliability.

■特 長

- ●この製品は逆回復時間を 0.4 μsec に押えスイッチング用として開発した素子で、テレビの水平偏回路等、高周波回路に最適です。
- ●構造はV03/V06で好評を博しましたガラスボデーですから組込み配線に大変便利であります。
- ●厳密な品質管理と安定した量産を行なっておりますので、特性は均一であり、極めて信頼度の高いダイオードです。



MAXIMUM ALLOWABLE RATINGS

	<u>Hitachi</u> Type		V11 J	V11L	V11M	V11N
Items Symbols Units	EIAJ No.		1 S 2323	1 S 2324	1 S 2325	1S 2326
Repetitive Peak Reverse Voltage	VRRM	V	800	1,000	1, 300	1,500
Non-repetitive Peak Reverse Voltage	VRSM	V	1,000	1, 300	1,600	1,800
Average Forward Current	Io	A	0.4 (Single-phase, half-wave 180° conduction ambient)			
Peak One-cycle Surge Current	ITSM	Α	25 (10msec conduction, sine half-wave 1 cycle)			
I ² t Limit Value	I²t	A ² sec	3.0 (Time=2~10msec. I=RMS value)			
Operating Temperature	Tj	c	$-40 \sim +125$			
Storage Temperature	Tstg	C	$-40 \sim +150$			
Weight		g	0. 35			

CHARACTERISTICS •

Items	Symbols	Units	Ratings		
Maximum Reverse Current	I _{RM}				
Maximum Forward Voltage Drop	V _{FM}	V	3.0 (Single-phase, half-wave peak value 1.6A, conduction)		
Reverse Recovery Time	trr	μsec	0.4 (T _j : 25°C, Measuring conditions are based on test circuit)		
Thermal Resistance	Rth	℃/W	(Junction to Air)		